

**INFORMATION DISCLOSURE  
CITATION**

ATTY. DOCKET NO.

SERIAL NO.

39230-0701

09/924,392

APPLICANT Atanackovic et al.

FILING DATE 08/07/01

GROUP 2633

PTO-1449

**U.S. PATENT DOCUMENTS**

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
	4,618,381	10/21/86	Sato et al.	148	189	
	5,039,190	8/13/91	Blonder et al.	359	341	
	5,119,460	6/2/92	Bruce et al.	385	142	
	5,473,174	12/5/95	Ohsawa	257	190	
	5,643,973	6/3/97	Cabral, Jr. et al.	117	95	
	5,646,425	7/8/97	Beach	257		

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OCT 11 2002  
Technology Center 2600

**FOREIGN PATENT DOCUMENTS**

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
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**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**


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SHEET 1 OF 1

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EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>[Signature]</i>	2002/0117573	3/29/02	Moon	257	79	

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**FOREIGN PATENT DOCUMENTS**

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
<i>[Signature]</i>	0 474 447 A1	03/11/92	Europe	G02B	6/10	<input type="checkbox"/>	<input type="checkbox"/>
<i>[Signature]</i>	0 517 440 A2	12/9/92	Europe	H01S	3/06	<input type="checkbox"/>	<input type="checkbox"/>
<i>[Signature]</i>	0 578 407 A1	1/12/94	Europe	H01S	3/06	<input type="checkbox"/>	<input type="checkbox"/>
<i>[Signature]</i>	5-283743	10/29/93	Japan	H01L	33/00	<input type="checkbox"/>	<input type="checkbox"/>
						<input type="checkbox"/>	<input type="checkbox"/>

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

<i>[Signature]</i>	Shin, J.H. et al., "Controlling the Quantum effects and Erbium-Carrier Interaction Using Si/SiO <sub>2</sub> /superlattices", RARE-EARTH-DOPED MATERIALS AND DEVICES, vol. 4282, Jan. 2001, pp. 142-152.
<i>[Signature]</i>	Orlov, L.K. et al., "Comparative Analysis of Light Emitting Properties of Si:Er and Ge/Si <sub>1-x</sub> Ge <sub>x</sub> /epitaxial Structures Obtained by MBE Method", GETTERING AND DEFECT ENGINEERING IN INTERNATIONAL AUTUMN MEETING, Sept. 1999, Vol. 69-70, pp. 377-382.
<i>[Signature]</i>	Favennec, P.N. et al., "Optical Activation of ER <sup>3+</sup> Implanted in Silicon By Oxygen Impurities", JAPANESE JOURNAL OF APPLIED PHYSICS, Vol. 29, No. 4, April 1990, pp. L524-L526.
<i>[Signature]</i>	Hak-Seung, H. et al., "Control of Location and Carrier-Interaction of Erbium Using Erbium-Doped Si/SiO <sub>2</sub> /superlattice", THIN FILMS FOR OPTICAL WAVEGUIDE DEVICES AND MATERIALS FOR OPTICAL LIMITING SYMPOSIUM, Vol. 597, pp. 29-30, 2000.
<i>[Signature]</i>	Ennen, H. et al., "1.54-μm Luminescence of Erbium-Implanted III-V Semiconductors and Silicon", APPLIED PHYSICS LETTERS, Vol. 43, No. 10, November 1983, pp. 943-945.
EXAMINER <i>[Signature]</i>	DATE CONSIDERED 4/03

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**INFORMATION DISCLOSURE  
STATEMENT**

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EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
	4,959,694	09/25/90	Gell	357	16	
	4,618,381	10/21/86	Sato et al.	148	189	
	5,033,816	07/23/91	Blondeau et al.	350	162	
	5,039,190	08/13/91	Blonder et al.	359	241	
	5,107,538	04/21/92	Benton et al.	385	130	
	5,119,460	06/02/92	Bruce et al.	385	142	
	5,181,211	01/19/93	Burnham et al.	372	2	
	5,262,656	11/16/93	Blondeau et al.	257	80	
	5,282,260	01/25/94	Buchal et al.	385	132	
	5,351,146	09/27/94	Chan et al.	359	118	
	5,355,237	10/11/94	Lang et al.	359	130	
	5,357,591	10/18/94	Jiang et al.	385	37	

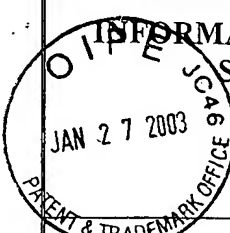
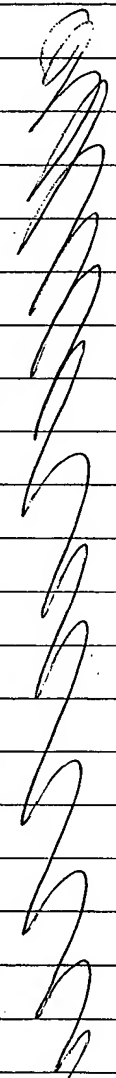


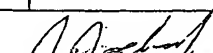
**FOREIGN PATENT DOCUMENTS**

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	0 474 447 A1	03/11/92	Europe	G02B	6/10	<input type="checkbox"/>	<input type="checkbox"/>
	0 517 440 A2	12/09/92	Europe	H01S	3/06	<input type="checkbox"/>	<input type="checkbox"/>
	0 578 407 A1	01/12/94	Europe	H01S	3/06	<input type="checkbox"/>	<input type="checkbox"/>
	1 215 781 A2	06/12/02	Europe	H01S	5/34	<input type="checkbox"/>	<input type="checkbox"/>

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

	Favennec P.N. et al., "Optical Activation of Er3+ Implanted in Silicon By Oxygen Impurities", Jap. Journ. App. Phys. Vol. 29, No. 4, April 1990, pp. 524-526.
	Han, H.S. et al., "Control of Location and Carrier-Interaction of Erbium Using Erbium-Doped Si/SiO2 Superlattice", Dep. Phys. Korea Advanced Institute of Sci. and Techn., November 30, 1999, pp. 27-32.
	Orlov, L.K. et al., "Comparative Analysis of Light Emitting Properties of Si:Er and Ge/Si1-xGex Epitaxial Structure Obtained by MBE Method", Inst. Phys. of Microstructures, (1999) pp. 377-382.
	Schneider, J. et al., "1.54-μm Luminescence of Erbium-implanted III-V Semiconductors and Silicon", Appl. Phys. Lett. 43(10), 15 November 1983, pp. 943-945.
EXAMINER	DATE CONSIDERED 4/03

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<b>INFORMATION DISCLOSURE STATEMENT</b> <b>PTO-1449</b> 		ATTY. DOCKET NO. <b>39230-0701</b>		SERIAL NO. <b>09/924,392</b>			
		APPLICANT Atanackovic et al.					
		FILING DATE 08/07/01		GROUP: 2803			
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
	5,468,684	11/21/95	Yoshimori et al.	457	228		
	5,473,174	12/5/95	Ohsawa	257	190		
	5,534,079	07/09/96	Beach	148	33		
	5,594,750	01/14/97	Zhang et al.	372	45		
	5,634,973	06/03/97	Cabral, Jr. et al.	117	95		
	5,646,425	07/08/97	Beach	257	102		
	5,647,038	07/08/97	Minden et al.	385	37		
	5,667,905	09/16/97	Campisano et al.	428	690		
	5,719,077	02/17/98	Chakrabarti et al.	438	129		
	5,719,416	02/17/98	Yoshimori et al.	257	295		
	5,852,346	12/22/98	Komoda et al.	315	169.3		
	5,917,195	06/29/99	Brown	257	22		
	5,920,078	06/06/99	Frey	257	14		
	5,942,050	08/24/99	Green et al.	136	258		
	6,058,131	05/2/00	Pan	372	102		
	6,069,908	05/30/00	Yuen et al.	372	96		
	6,403,975	06/11/02	Brunner et al.	257	15		
	6,456,423	09/24/02	Nayfeh et al.	359	328		
	2002/0017657	02/14/02	Coffa et al.	257	200		
	2002/0096675	07/25/02	Cho et al.	257	25		
<b>FOREIGN PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
	5-283743	04/03/92	Japan	H01L	33/00	<input type="checkbox"/>	<input type="checkbox"/>
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
	Shin, J.H. et al., "Controlling the Quantum Effects and Erbium-Carrier Interaction Using Si/SiO <sub>2</sub> Superlattices", Dept. of Phys. Korea Advanced Institute, January 22, 2001, pp. 142-152.						
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**Notice of References Cited**

Application/Control No.

09/924,392

Applicant(s)/Patent Under  
Reexamination  
ATANACKOVIC ET AL.

Examiner

Jerome Jackson Jr.

Art Unit

2815

Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-5,363,398	11-1994	Glass et al	372/92
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	
	V	
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.